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IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

a semiconductor IC chip ~~provided with an electrode pad~~
comprising a plurality of electrode pads, said pads each having
a side;

an insulating layer ~~formed~~ located on a surface of the
semiconductor IC chip, on ~~the side of~~ a surface of each of the
electrode pads;

a connecting terminal on an outer surface of the insulating
layer; and

a conductive post extending through the insulating layer
and connecting the electrode pad of the semiconductor IC chip to
the connecting ~~terminal;~~ terminal,

wherein the insulating layer ~~is formed of~~ comprises an
insulating elastic material and the conductive post comprises a
conductive elastic material.

2. (Canceled)

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3. (Currently Amended) The semiconductor device according to claim 21, wherein

~~the conductive elastic material of the conductive post~~
containsconductive post comprises a synthetic rubber and
conductive particles dispersed in the synthetic rubber.

4. (Currently Amended) The semiconductor device according to claim 3, wherein

the conductive elastic material of the conductive post ~~is~~
comprises a composite paste ~~containing~~comprising an addition-
polymerized silicone rubber, and at least 70% by weight ~~or above~~
Ag particles dispersed in the addition-polymerized silicone
rubber, and

the composite paste ~~as~~when cured has a volume resistivity
of not more than $5 \times 10^{-3} \Omega \cdot \text{cm}$ ~~or below~~.

5. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~further comprising:

a wiring layer ~~is formed~~located between ~~the~~an electrode
pad of the semiconductor IC chip and the conductive post.

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6. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~ further comprising:

a wiring part ~~is formed~~ located between the connecting terminal and the conductive post.

7. (Original) The semiconductor device according to claim 1, wherein the connecting terminal is a solder ball.

8. (Currently Amended) The semiconductor device according to claim 7, ~~wherein~~ further comprising:

a barrier metal layer ~~is provided~~ located between the solder ball and the conductive post.

9. (Currently Amended) The semiconductor device according to claim 1, wherein

the insulating elastic material of the insulating layer is ~~any one~~ selected from the group consisting of silicone rubber, fluororubber, polyurethane rubber, polybutadiene rubber,

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acrylonitrile-butadiene copolymer and polyisoprene rubber, and has an elastic modulus of not more than 100 MPa ~~or below~~.

10. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~ further comprising:

a protective layer on the outer surface of the insulating layer ~~of the insulating elastic material is coated with a protective layer~~ of the insulating layer, and ~~a part of~~

~~the connecting terminal lies~~ comprises a portion located at a position on the protective layer.

11. (Currently Amended) The semiconductor device according to claim 10, wherein

the protective layer ~~is formed of~~ comprises a material selected from the group consisting of a polyimide resin, a liquid crystalline polymer ~~or~~ and an epoxy solder resist.

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12. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~comprising:

~~the semiconductor device is a~~ wafer-level chip-scale package produced by cutting a wafer ~~with~~into a plurality of semiconductor IC chips.

13.-17. (Canceled)